



## 100V/2.6A N-Channel Advanced Power MOSFET

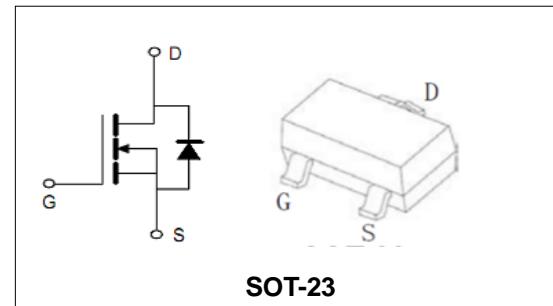
**Features**

- High density cell design for ultra low Rdson

**Applications**

- Power switching application
- Hard switched and high frequency circuits
- Uninterruptible power supply

BVDSS	100	V
ID	2.6	A
RDSON@VGS=10V	115	mΩ
RDSON@VGS=4.5V	135	mΩ

**Order Information**

Product	Package	Marking	Reel Size	Reel	Carton
PTL03N10	SOT-23	3N10	7inch	3000PCS	180000PCS

**Absolute Maximum Ratings**

Symbol	Parameter	Rating	Unit	
<b>Common Ratings (TC=25°C Unless Otherwise Noted)</b>				
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	100	V	
$V_{GS}$	Gate-Source Voltage	$\pm 20$	V	
$T_J$	Maximum Junction Temperature	150	°C	
$T_{STG}$	Storage Temperature Range	-55 to 150	°C	
$I_S$	Diode Continuous Forward Current	TC =25°C	2.6	A
<b>Mounted on Large Heat Sink</b>				
$I_{DM}$	Pulse Drain Current Tested (Silicon Limit) (Note1)	TC =25°C	10	A
$I_D$	Continuous Drain current	TC =25°C	2.6	A
$P_D$	Maximum Power Dissipation	TC =25°C	1	W
$R_{θJA}$	Thermal Resistance Junction-to-Ambient (Note2)		125	°C/W

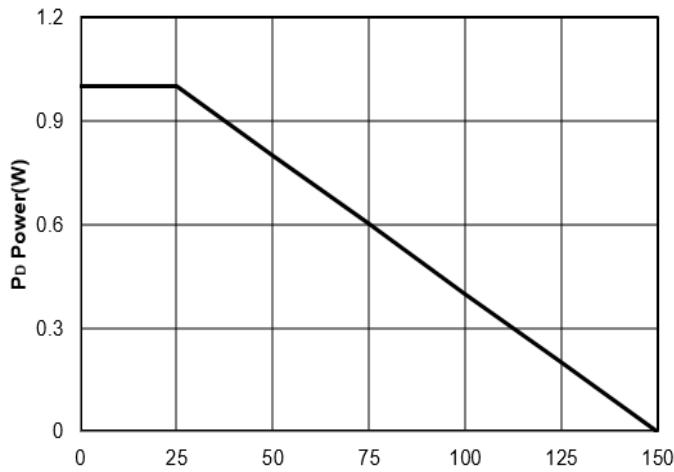
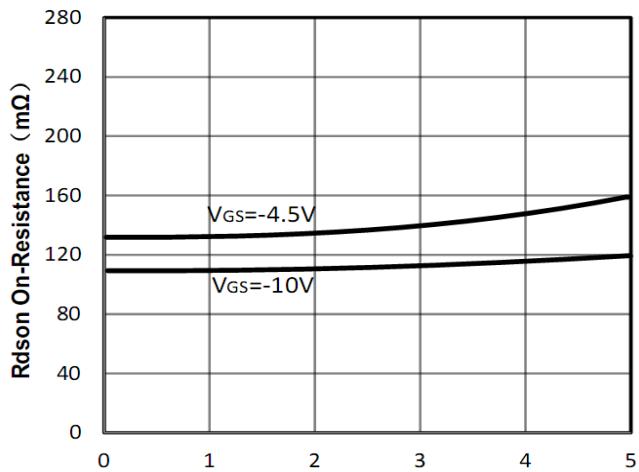
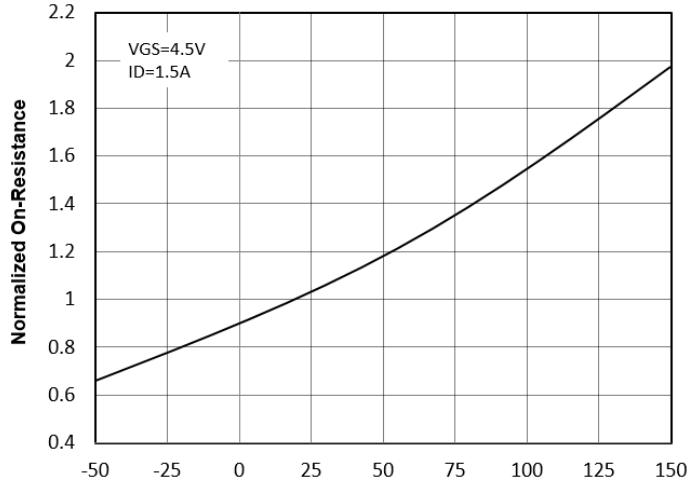
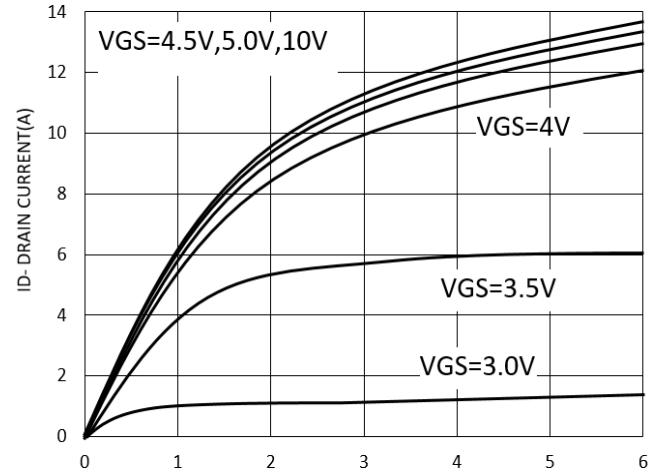
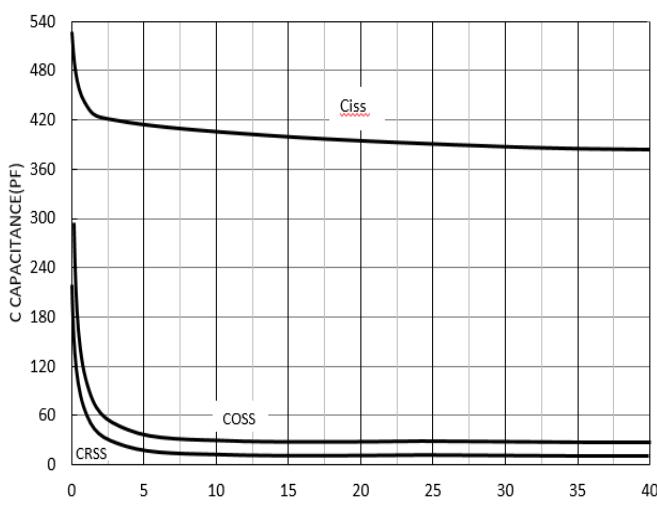
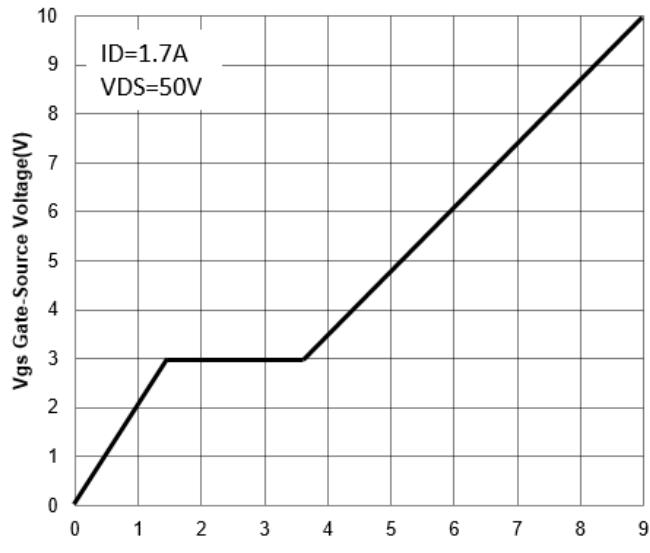


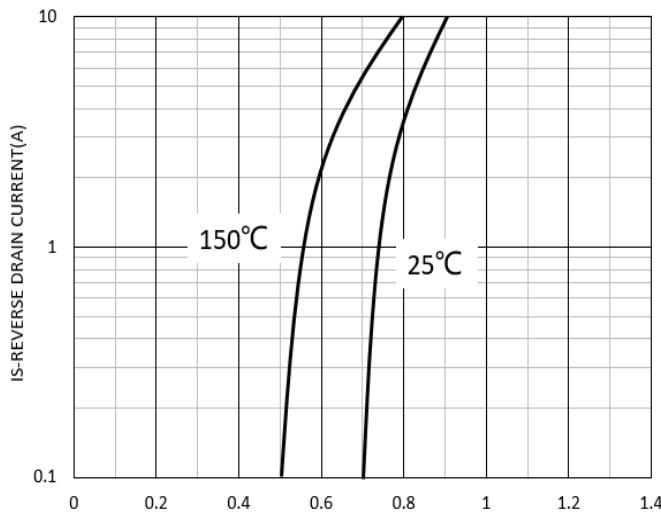
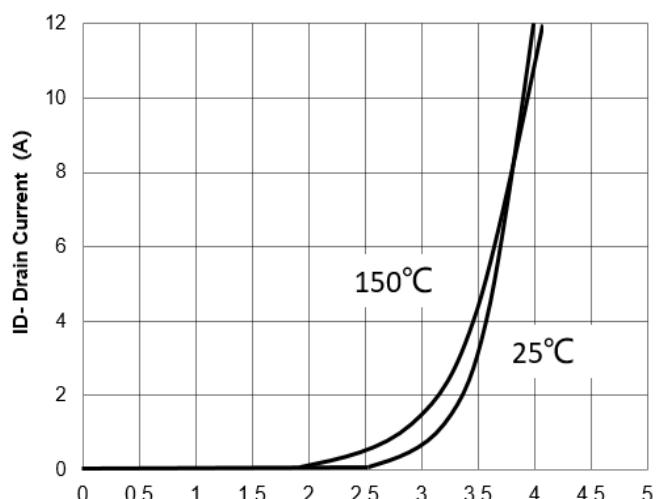
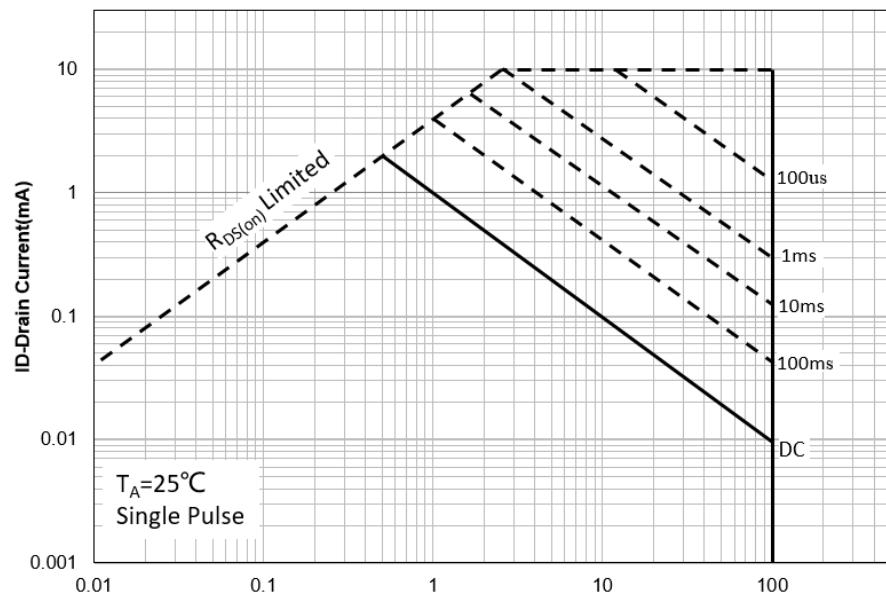
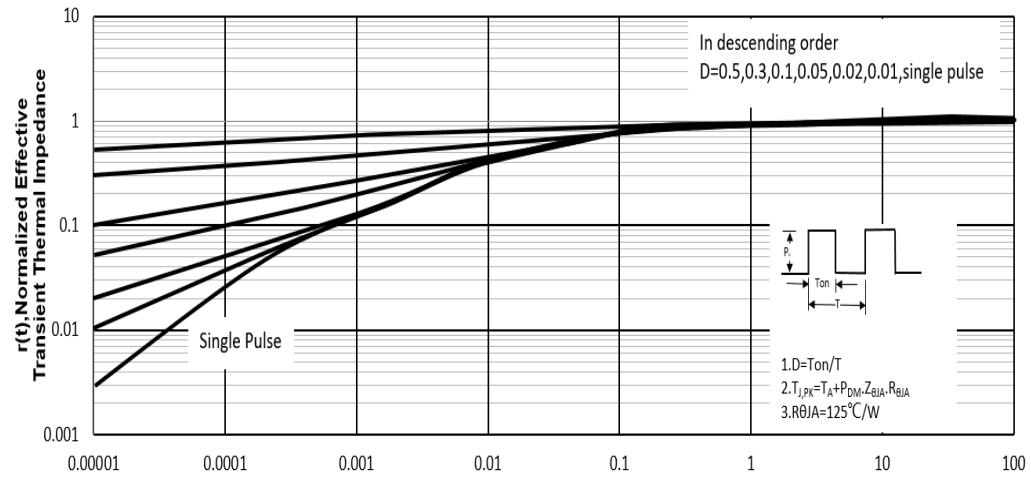
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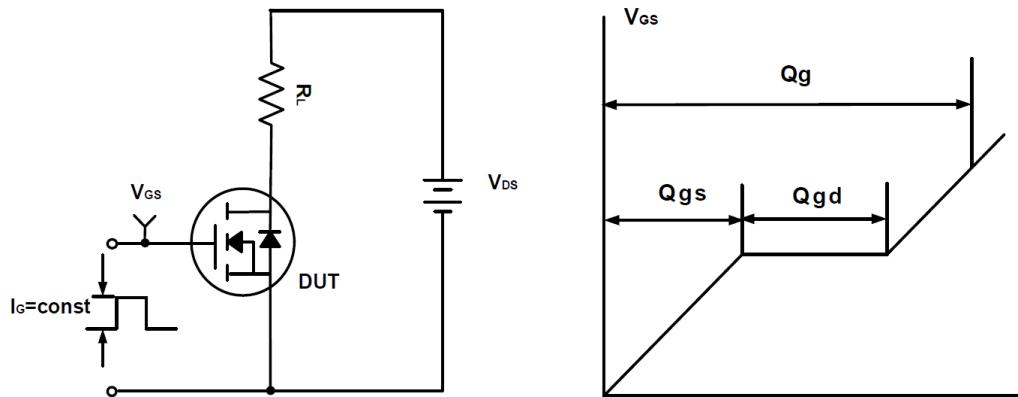
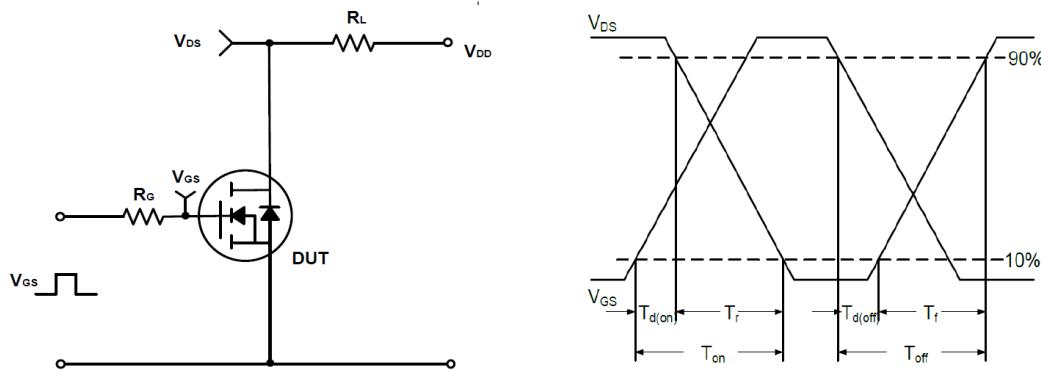
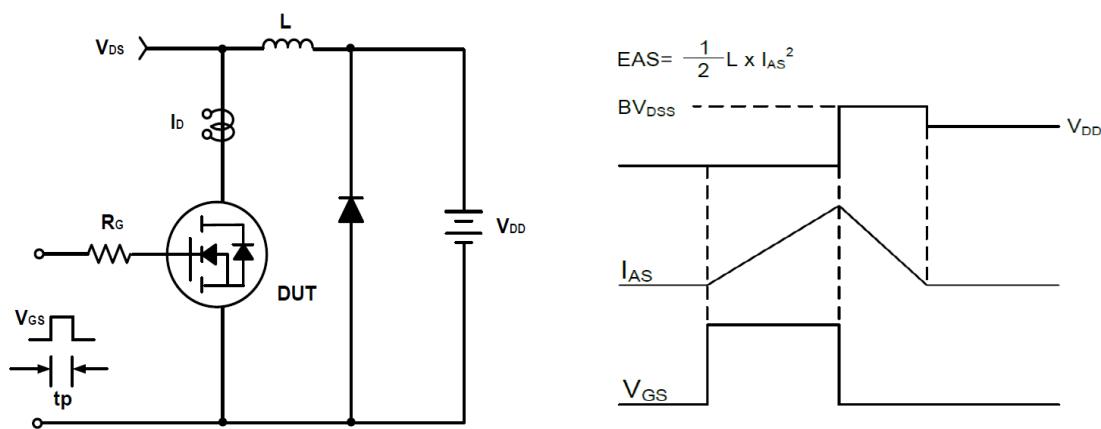
Symbol	Parameter	Condition	Min.	Typ.	Max.	Unit
<b>Static Electrical Characteristics @ TJ = 25°C (unless otherwise stated)</b>						
$V_{(BR)DSS}$	Drain- Source Breakdown Voltage	$VGS=0V$ $ID=250\mu A$	100	--	--	V
$I_{DSS}$	Zero Gate Voltage Drain current	$VDS=100V, VGS=0V$	--	--	1	$\mu A$
$I_{GSS}$	Gate-Body Leakage Current	$VGS=\pm 20V, VDS=0V$	--	--	$\pm 100$	nA
$V_{GS(TH)}$	Gate Threshold Voltage	$VDS=VGS, ID=250\mu A$	1	1.8	3	V
$R_{DS(ON)}$	Drain-Source On-State Resistance (Note3)	$VGS=10V, ID=2.5A$	--	115	165	$m\Omega$
		$VGS=4.5V, ID=1.5A$	--	135	180	$m\Omega$
<b>Dynamic Electrical Characteristics @ TJ = 25°C (unless otherwise stated) (Note4)</b>						
$C_{iss}$	Input Capacitance	$VDS=30V,$ $VGS=0V,$ $F=1MHz$	--	405	--	pF
$C_{oss}$	Output Capacitance		--	36	--	pF
$C_{rss}$	Reverse Transfer Capacitance		--	18	--	pF
$Q_g$	Total Gate Charge	$VGS=10V,$ $VDS=30V,$ $ID=1 A$	--	9	--	nC
$Q_{gs}$	Gate-Source Charge		--	1.5	--	nC
$Q_{gd}$	Gate-Drain Charge		--	2.1	--	nC
<b>Switching Characteristics (Note4)</b>						
$t_{d(on)}$	Turn-on Delay Time	$VDS=30V,$ $ID=1A,$ $RG=6.8\Omega,$ $VGS=10V$	--	9	--	nS
$t_r$	Turn-on Rise Time		--	8.1	--	nS
$t_{d(off)}$	Turn-off Delay Time		--	20	--	nS
$t_f$	Turn-off Fall Time		--	13.5	--	nS
<b>Source- Drain Diode Characteristics@ TJ = 25°C (unless otherwise stated)</b>						
$V_{SD}$	Forward on voltage	$IS=2.5A, VGS=0V$	--	--	1.3	V

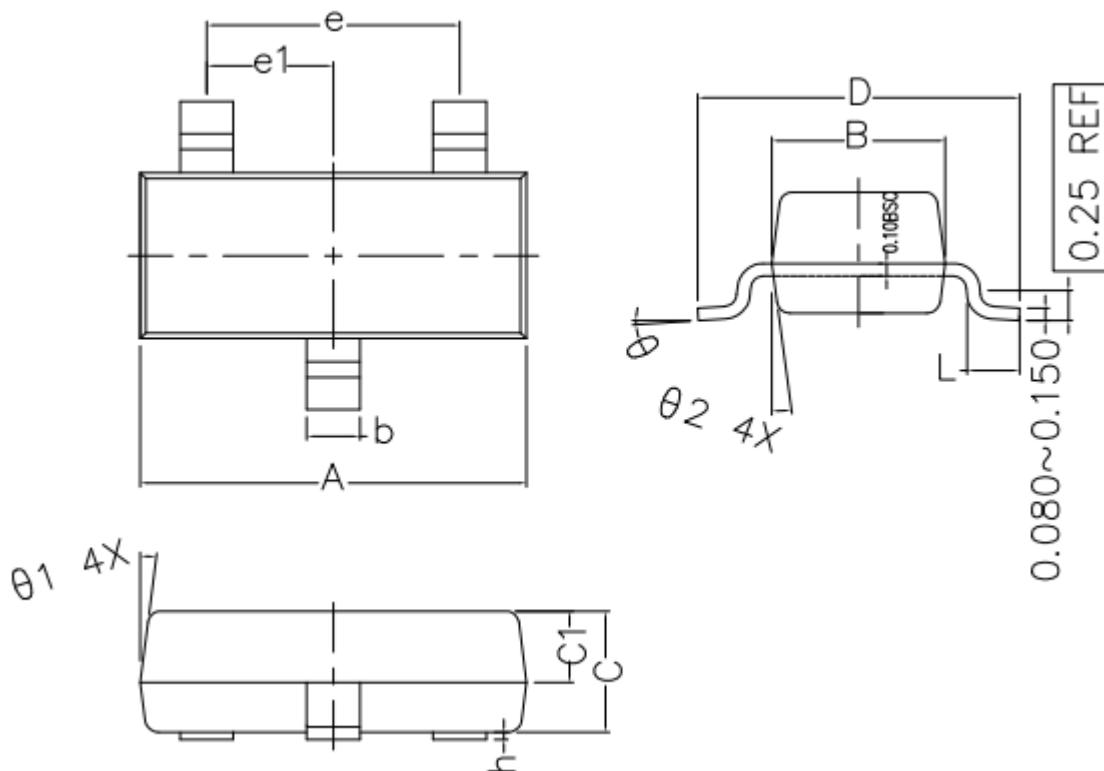
Note:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board,  $t \leq 10$  sec.
3. Pulse Test: pulse width  $\leq 300$  us, duty cycle  $\leq 2\%$ .
4. Guranteed by design, not subject to production testing.

**100V/2.6A N-Channel Advanced Power MOSFET**
**Typical Characteristics**

**Figure1: T<sub>J</sub> Junction Temperature (°C)**

**Figure2: I<sub>D</sub> Drain Current (A)**

**Figure3: T<sub>J</sub> Junction Temperature (°C)**

**Figure4: V<sub>DS</sub> Drain-Source Voltage (V)**

**Figure5: V<sub>DS</sub> Drain-Source Voltage (V)**

**Figure6: Q<sub>g</sub> Gate Charge (nC)**

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**Figure7: Vsd Source-Drain Voltage (V)**

**Figure8: Vgs Gate-Source Voltage (V)**

**Figure9: Vsd Drain -Source Voltage (V)**

**Figure10: Square Wave Pulse Duration (sec)**

**100V/2.6A N-Channel Advanced Power MOSFET**
**Test Circuit and Waveform:**

**Figure A Gate Charge Test Circuit & Waveforms**

**Figure B Switching Test Circuit & Waveforms**

**Figure C Unclamped Inductive Switching Circuit & Waveforms**

**100V/2.6A N-Channel Advanced Power MOSFET**
**SOT-23 Package Outline Dimensions (Units: mm)**


COMMON DIMENSIONS (UNITS OF MEASURE IS mm)			
	MIN	NORMAL	MAX
A	2.800	2.900	3.000
B	1.200	1.300	1.400
C	0.900	1.000	1.100
C1	0.500	0.550	0.600
D	2.250	2.400	2.550
L	0.300	0.400	0.500
h	0.010	0.050	0.100
b	0.300	0.400	0.500
e	1.90 TYPE		
e1	0.95 TYPE		
$\theta_1$	7° TYPE		
$\theta_2$	7° TYPE		
$\theta$	$0^\circ \sim 7^\circ$		